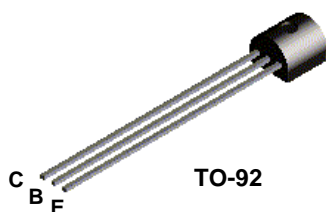
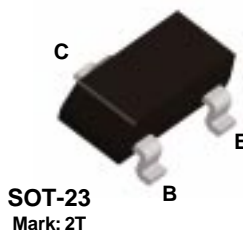


2N4403



MMBT4403



PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 40 | V |
| V _{CBO} | Collector-Base Voltage | 40 | V |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V |
| I _C | Collector Current - Continuous | 600 | mA |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | | Units |
|------------------|---|--------|-----------|-------|
| | | 2N4403 | *MMBT4403 | |
| P _D | Total Device Dissipation | 625 | 350 | mW |
| | Derate above 25°C | 5.0 | 2.8 | mW/°C |
| R _{θJC} | Thermal Resistance, Junction to Case | 83.3 | | °C/W |
| R _{θJA} | Thermal Resistance, Junction to Ambient | 200 | 357 | °C/W |

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP General Purpose Amplifier

(continued)

2N4403 / MMBT4403

Electrical Characteristics

TA = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|--------|-----------|-----------------|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-------|

OFF CHARACTERISTICS

| | | | | | |
|---------------|--------------------------------------|---|-----|-----|---------------|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage* | $I_C = 1.0 \text{ mA}, I_B = 0$ | 40 | | V |
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C = 0.1 \text{ mA}, I_E = 0$ | 40 | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E = 0.1 \text{ A}, I_C = 0$ | 5.0 | | V |
| I_{BEX} | Base Cutoff Current | $V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$ | | 0.1 | μA |
| I_{CEX} | Collector Cutoff Current | $V_{CE} = 35 \text{ V}, V_{BE} = 0.4 \text{ V}$ | | 0.1 | μA |

ON CHARACTERISTICS

| | | | | | |
|---------------|---------------------------------------|---|------------------------------|-------------|--------|
| h_{FE} | DC Current Gain | $I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$ $I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$ | 30 60 100 100 20 | 300 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage* | $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | 0.4 0.75 | V V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^*$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | 0.75 | 0.95 1.3 | V V |

SMALL SIGNAL CHARACTERISTICS

| | | | | | |
|----------|----------------------------------|---|-----|-----|------------------|
| f_T | Current Gain - Bandwidth Product | $I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ | 200 | | MHz |
| C_{cb} | Collector-Base Capacitance | $V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 140 \text{ kHz}$ | | 8.5 | pF |
| C_{eb} | Emitter-Base Capacitance | $V_{BE} = 0.5 \text{ V}, I_C = 0,$ $f = 140 \text{ kHz}$ | | 30 | pF |
| h_{ie} | Input Impedance | $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$ | 1.5 | 15 | $k\Omega$ |
| h_{re} | Voltage Feedback Ratio | $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$ | 0.1 | 8.0 | $\times 10^{-4}$ |
| h_{fe} | Small-Signal Current Gain | $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$ | 60 | 500 | |
| h_{oe} | Output Admittance | $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$ | 1.0 | 100 | μmhos |

SWITCHING CHARACTERISTICS

| | | | | | |
|-------|--------------|--|--|-----|----|
| t_d | Delay Time | $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA},$ | | 15 | ns |
| t_r | Rise Time | $I_{B1} = 15 \text{ mA}$ | | 20 | ns |
| t_s | Storage Time | $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$ | | 225 | ns |
| t_f | Fall Time | $I_{B1} = I_{B2} = 15 \text{ mA}$ | | 30 | ns |

*Pulse Test: Pulse Width $\leq 300 \text{ ms}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

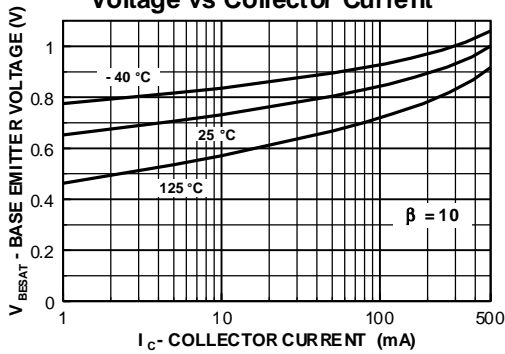
Typical Pulsed Current Gain vs Collector Current



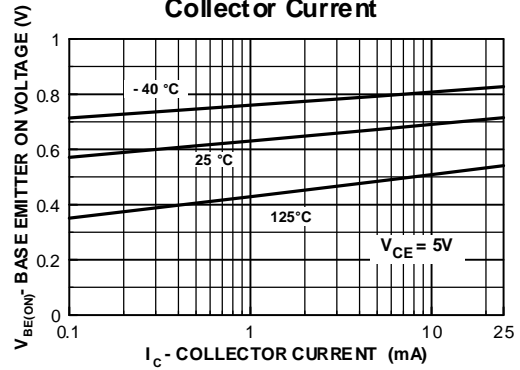
Collector-Emitter Saturation Voltage vs Collector Current



Base-Emitter Saturation Voltage vs Collector Current



Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



Input and Output Capacitance vs Reverse Bias Voltage

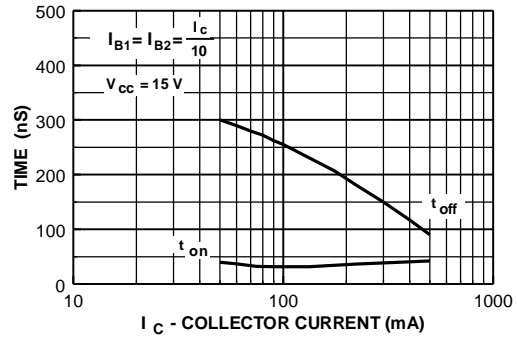


Typical Characteristics (continued)

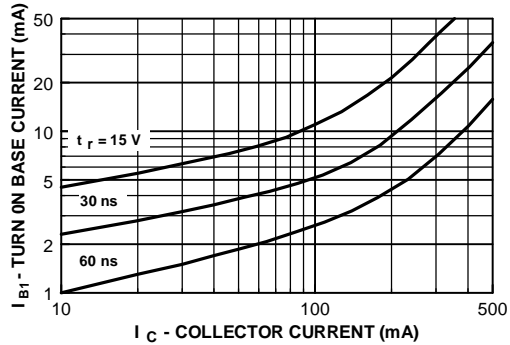
Switching Times vs Collector Current



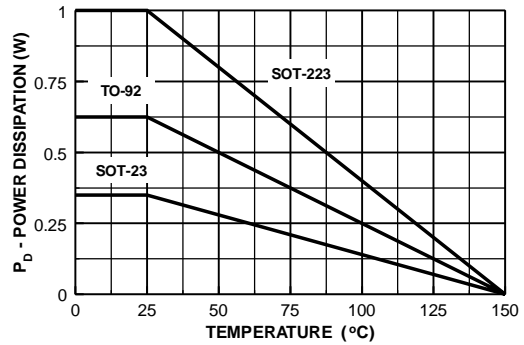
Turn On and Turn Off Times vs Collector Current



Rise Time vs Collector and Turn On Base Currents



Power Dissipation vs Ambient Temperature



PNP General Purpose Amplifier
(continued)

2N4403 / MMBT4403

Typical Common Emitter Characteristics (f = 1.0kHz)



Test Circuits

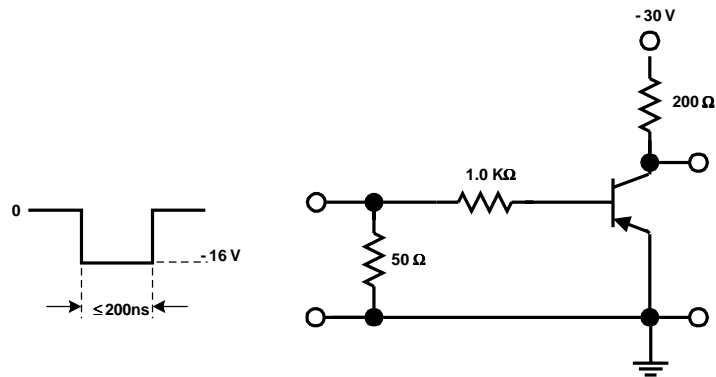


FIGURE 1: Saturated Turn-On Switching Time Test Circuit



FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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